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Understanding **Embedded - FPGAs (Field Programmable Gate Array)**

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

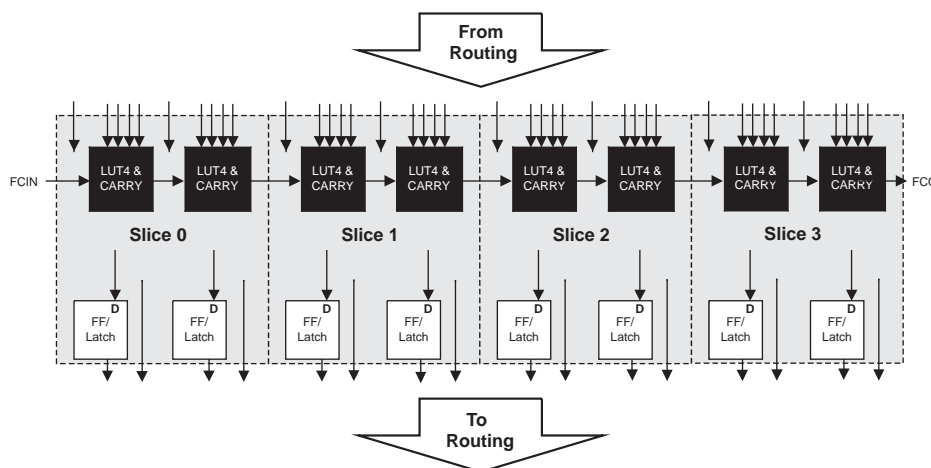
Details

Product Status	Active
Number of LABs/CLBs	1175
Number of Logic Elements/Cells	9400
Total RAM Bits	442368
Number of I/O	384
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-LFBGA
Supplier Device Package	484-CABGA (19x19)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo3l-9400e-6bg484i

PFU Blocks

The core of the MachXO3L/LF device consists of PFU blocks, which can be programmed to perform logic, arithmetic, distributed RAM and distributed ROM functions. Each PFU block consists of four interconnected slices numbered 0 to 3 as shown in Figure 2-3. Each slice contains two LUTs and two registers. There are 53 inputs and 25 outputs associated with each PFU block.

Figure 2-3. PFU Block Diagram



Slices

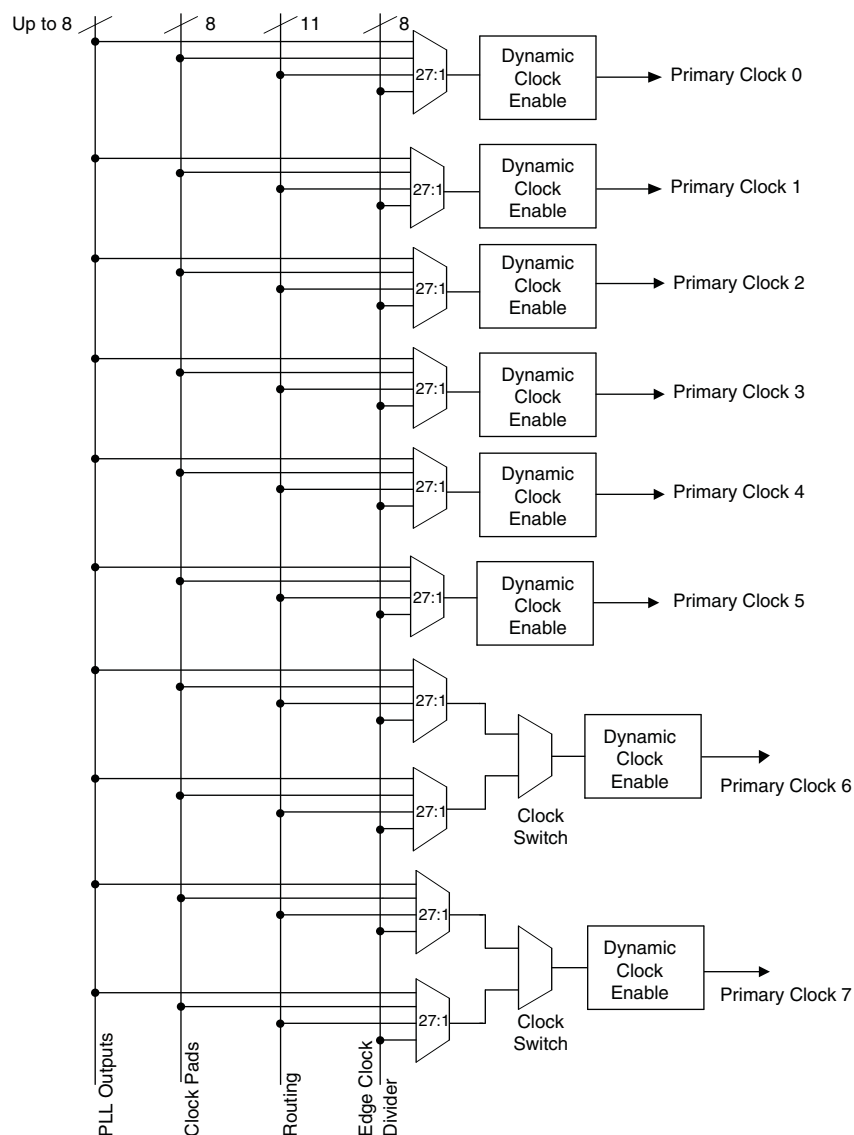
Slices 0-3 contain two LUT4s feeding two registers. Slices 0-2 can be configured as distributed memory. Table 2-1 shows the capability of the slices in PFU blocks along with the operation modes they enable. In addition, each PFU contains logic that allows the LUTs to be combined to perform functions such as LUT5, LUT6, LUT7 and LUT8. The control logic performs set/reset functions (programmable as synchronous/ asynchronous), clock select, chip-select and wider RAM/ROM functions.

Table 2-1. Resources and Modes Available per Slice

Slice	PFU Block	
	Resources	Modes
Slice 0	2 LUT4s and 2 Registers	Logic, Ripple, RAM, ROM
Slice 1	2 LUT4s and 2 Registers	Logic, Ripple, RAM, ROM
Slice 2	2 LUT4s and 2 Registers	Logic, Ripple, RAM, ROM
Slice 3	2 LUT4s and 2 Registers	Logic, Ripple, ROM

Figure 2-4 shows an overview of the internal logic of the slice. The registers in the slice can be configured for positive/negative and edge triggered or level sensitive clocks. All slices have 15 inputs from routing and one from the carry-chain (from the adjacent slice or PFU). There are seven outputs: six for routing and one to carry-chain (to the adjacent PFU). Table 2-2 lists the signals associated with Slices 0-3.

Figure 2-5. Primary Clocks for MachXO3L/LF Devices



Eight secondary high fanout nets are generated from eight 8:1 muxes as shown in Figure 2-6. One of the eight inputs to the secondary high fanout net input mux comes from dual function clock pins and the remaining seven come from internal routing. The maximum frequency for the secondary clock network is shown in MachXO3L/LF External Switching Characteristics table.

If an EBR is pre-loaded during configuration, the GSR input must be disabled or the release of the GSR during device wake up must occur before the release of the device I/Os becoming active.

These instructions apply to all EBR RAM, ROM and FIFO implementations. For the EBR FIFO mode, the GSR signal is always enabled and the WE and RE signals act like the clock enable signals in Figure 2-10. The reset timing rules apply to the RPRreset input versus the RE input and the RST input versus the WE and RE inputs. Both RST and RPRreset are always asynchronous EBR inputs. For more details refer to TN1290, [Memory Usage Guide for MachXO3 Devices](#).

Note that there are no reset restrictions if the EBR synchronous reset is used and the EBR GSR input is disabled.

Programmable I/O Cells (PIC)

The programmable logic associated with an I/O is called a PIO. The individual PIO are connected to their respective sysIO buffers and pads. On the MachXO3L/LF devices, the PIO cells are assembled into groups of four PIO cells called a Programmable I/O Cell or PIC. The PICs are placed on all four sides of the device.

On all the MachXO3L/LF devices, two adjacent PIOs can be combined to provide a complementary output driver pair.

All PIO pairs can implement differential receivers. Half of the PIO pairs on the top edge of these devices can be configured as true LVDS transmit pairs. The PIO pairs on the bottom edge of these devices have on-chip differential termination and also provide PCI support.

Table 2-11 shows the I/O standards (together with their supply and reference voltages) supported by the MachXO3L/LF devices. For further information on utilizing the sysIO buffer to support a variety of standards please see TN1280, [MachXO3 sysIO Usage Guide](#).

Table 2-11. Supported Input Standards

Input Standard	VCCIO (Typ.)				
	3.3 V	2.5 V	1.8 V	1.5 V	1.2 V
Single-Ended Interfaces					
LVTTTL	Yes				
LVC MOS33	Yes				
LVC MOS25		Yes			
LVC MOS18			Yes		
LVC MOS15				Yes	
LVC MOS12					Yes
PCI	Yes				
Differential Interfaces					
LVDS	Yes	Yes			
BLVDS, MLVDS, LVPECL, RSDS	Yes	Yes			
MIPI ¹	Yes	Yes			
LVTTLD	Yes				
LVC MOS33D	Yes				
LVC MOS25D		Yes			
LVC MOS18D			Yes		

1. These interfaces can be emulated with external resistors in all devices.

There are some limitations on the use of the hardened user SPI. These are defined in the following technical notes:

- TN1087, [Minimizing System Interruption During Configuration Using TransFR Technology](#) (Appendix B)
- TN1293, [Using Hardened Control Functions in MachXO3 Devices](#)

Figure 2-19. SPI Core Block Diagram

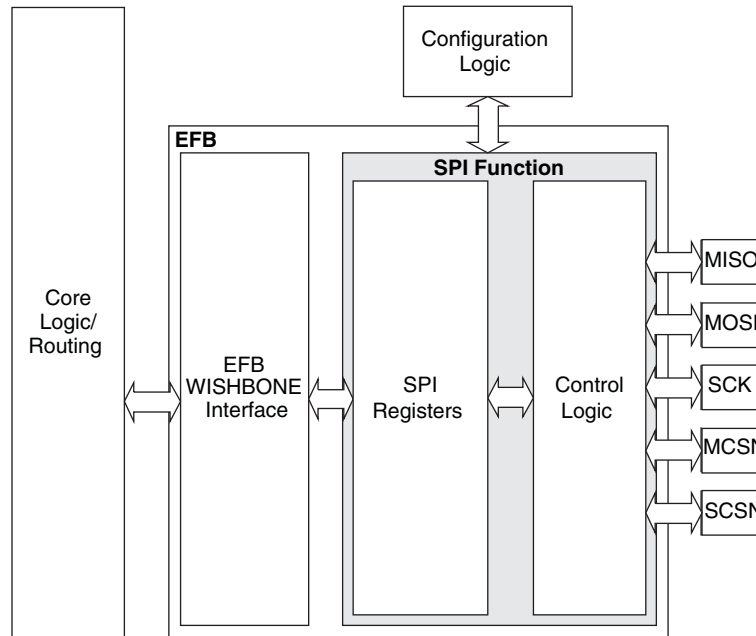


Table 2-15 describes the signals interfacing with the SPI cores.

Table 2-15. SPI Core Signal Description

Signal Name	I/O	Master/Slave	Description
spi_csn[0]	O	Master	SPI master chip-select output
spi_csn[1..7]	O	Master	Additional SPI chip-select outputs (total up to eight slaves)
spi_scsn	I	Slave	SPI slave chip-select input
spi_irq	O	Master/Slave	Interrupt request
spi_clk	I/O	Master/Slave	SPI clock. Output in master mode. Input in slave mode.
spi_miso	I/O	Master/Slave	SPI data. Input in master mode. Output in slave mode.
spi_mosi	I/O	Master/Slave	SPI data. Output in master mode. Input in slave mode.
sn	I	Slave	Configuration Slave Chip Select (active low), dedicated for selecting the Configuration Logic.
cfg_stdbby	O	Master/Slave	Stand-by signal – To be connected only to the power module of the MachXO3L/LF device. The signal is enabled only if the “Wakeup Enable” feature has been set within the EFB GUI, SPI Tab.
cfg_wake	O	Master/Slave	Wake-up signal – To be connected only to the power module of the MachXO3L/LF device. The signal is enabled only if the “Wakeup Enable” feature has been set within the EFB GUI, SPI Tab.

For more details on these embedded functions, please refer to TN1293, [Using Hardened Control Functions in MachXO3 Devices](#).

User Flash Memory (UFM)

MachXO3LF devices provide a User Flash Memory block, which can be used for a variety of applications including storing a portion of the configuration image, initializing EBRs, to store PROM data or, as a general purpose user Flash memory. The UFM block connects to the device core through the embedded function block WISHBONE interface. Users can also access the UFM block through the JTAG, I2C and SPI interfaces of the device. The UFM block offers the following features:

- Non-volatile storage up to 256 kbits
- 100K write cycles
- Write access is performed page-wise; each page has 128 bits (16 bytes)
- Auto-increment addressing
- WISHBONE interface

For more information on the UFM, please refer to TN1293, [Using Hardened Control Functions in MachXO3 Devices](#).

Standby Mode and Power Saving Options

MachXO3L/LF devices are available in two options, the C and E devices. The C devices have a built-in voltage regulator to allow for 2.5 V V_{CC} and 3.3 V V_{CC} while the E devices operate at 1.2 V V_{CC} .

MachXO3L/LF devices have been designed with features that allow users to meet the static and dynamic power requirements of their applications by controlling various device subsystems such as the bandgap, power-on-reset circuitry, I/O bank controllers, power guard, on-chip oscillator, PLLs, etc. In order to maximize power savings, MachXO3L/LF devices support a low power Stand-by mode.

In the stand-by mode the MachXO3L/LF devices are powered on and configured. Internal logic, I/Os and memories are switched on and remain operational, as the user logic waits for an external input. The device enters this mode when the standby input of the standby controller is toggled or when an appropriate I²C or JTAG instruction is issued by an external master. Various subsystems in the device such as the band gap, power-on-reset circuitry etc can be configured such that they are automatically turned “off” or go into a low power consumption state to save power when the device enters this state. Note that the MachXO3L/LF devices are powered on when in standby mode and all power supplies should remain in the Recommended Operating Conditions.

Configuration and Testing

This section describes the configuration and testing features of the MachXO3L/LF family.

IEEE 1149.1-Compliant Boundary Scan Testability

All MachXO3L/LF devices have boundary scan cells that are accessed through an IEEE 1149.1 compliant test access port (TAP). This allows functional testing of the circuit board, on which the device is mounted, through a serial scan path that can access all critical logic nodes. Internal registers are linked internally, allowing test data to be shifted in and loaded directly onto test nodes, or test data to be captured and shifted out for verification. The test access port consists of dedicated I/Os: TDI, TDO, TCK and TMS. The test access port shares its power supply with V_{CCIO} Bank 0 and can operate with LVCMOS3.3, 2.5, 1.8, 1.5, and 1.2 standards.

For more details on boundary scan test, see AN8066, [Boundary Scan Testability with Lattice sysIO Capability](#) and TN1087, [Minimizing System Interruption During Configuration Using TransFR Technology](#).

Device Configuration

All MachXO3L/LF devices contain two ports that can be used for device configuration. The Test Access Port (TAP), which supports bit-wide configuration and the sysCONFIG port which supports serial configuration through I²C or SPI. The TAP supports both the IEEE Standard 1149.1 Boundary Scan specification and the IEEE Standard 1532 In-System Configuration specification. There are various ways to configure a MachXO3L/LF device:

1. Internal NVCM/Flash Download
2. JTAG
3. Standard Serial Peripheral Interface (Master SPI mode) – interface to boot PROM memory
4. System microprocessor to drive a serial slave SPI port (SSPI mode)
5. Standard I²C Interface to system microprocessor

Upon power-up, the configuration SRAM is ready to be configured using the selected sysCONFIG port. Once a configuration port is selected, it will remain active throughout that configuration cycle. The IEEE 1149.1 port can be activated any time after power-up by sending the appropriate command through the TAP port. Optionally the device can run a CRC check upon entering the user mode. This will ensure that the device was configured correctly.

The sysCONFIG port has 10 dual-function pins which can be used as general purpose I/Os if they are not required for configuration. See TN1279, [MachXO3 Programming and Configuration Usage Guide](#) for more information about using the dual-use pins as general purpose I/Os.

Lattice design software uses proprietary compression technology to compress bit-streams for use in MachXO3L/LF devices. Use of this technology allows Lattice to provide a lower cost solution. In the unlikely event that this technology is unable to compress bitstreams to fit into the amount of on-chip NVCM/Flash, there are a variety of techniques that can be utilized to allow the bitstream to fit in the on-chip NVCM/Flash. For more details, refer to TN1279, [MachXO3 Programming and Configuration Usage Guide](#).

The Test Access Port (TAP) has five dual purpose pins (TDI, TDO, TMS, TCK and JTAGENB). These pins are dual function pins - TDI, TDO, TMS and TCK can be used as general purpose I/O if desired. For more details, refer to TN1279, [MachXO3 Programming and Configuration Usage Guide](#).

TransFR (Transparent Field Reconfiguration)

TransFR is a unique Lattice technology that allows users to update their logic in the field without interrupting system operation using a simple push-button solution. For more details refer to TN1087, [Minimizing System Interruption During Configuration Using TransFR Technology](#) for details.

TraceID

Each MachXO3L/LF device contains a unique (per device), TraceID that can be used for tracking purposes or for IP security applications. The TraceID is 64 bits long. Eight out of 64 bits are user-programmable, the remaining 56 bits are factory-programmed. The TraceID is accessible through the EFB WISHBONE interface and can also be accessed through the SPI, I²C, or JTAG interfaces.

Density Shifting

The MachXO3L/LF family has been designed to enable density migration within the same package. Furthermore, the architecture ensures a high success rate when performing design migration from lower density devices to higher density devices. In many cases, it is also possible to shift a lower utilization design targeted for a high-density device to a lower density device. However, the exact details of the final resource utilization will impact the likely success in each case. When migrating from lower to higher density or higher to lower density, ensure to review all the power supplies and NC pins of the chosen devices. For more details refer to the [MachXO3 migration files](#).

Power-On-Reset Voltage Levels^{1, 2, 3, 4, 5}

Symbol	Parameter	Min.	Typ.	Max.	Units
V_{PORUP}	Power-On-Reset ramp up trip point (band gap based circuit monitoring V_{CCINT} and V_{CCIO0})	0.9	—	1.06	V
$V_{PORUPEXT}$	Power-On-Reset ramp up trip point (band gap based circuit monitoring external V_{CC} power supply)	1.5	—	2.1	V
$V_{PORDNBG}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CCINT})	0.75	—	0.93	V
$V_{PORDNBGEXT}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CC})	0.98	—	1.33	V
$V_{PORDNSRAM}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CCINT})	—	0.6	—	V
$V_{PORDNSRAMEXT}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CC})	—	0.96	—	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.
2. For devices without voltage regulators V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage.
3. Note that V_{PORUP} (min.) and $V_{PORDNBG}$ (max.) are in different process corners. For any given process corner $V_{PORDNBG}$ (max.) is always 12.0 mV below V_{PORUP} (min.).
4. $V_{PORUPEXT}$ is for C devices only. In these devices a separate POR circuit monitors the external V_{CC} power supply.
5. V_{CCIO0} does not have a Power-On-Reset ramp down trip point. V_{CCIO0} must remain within the Recommended Operating Conditions to ensure proper operation.

Hot Socketing Specifications^{1, 2, 3}

Symbol	Parameter	Condition	Max.	Units
I_{DK}	Input or I/O leakage Current	$0 < V_{IN} < V_{IH}$ (MAX)	+/-1000	μA

1. Insensitive to sequence of V_{CC} and V_{CCIO} . However, assumes monotonic rise/fall rates for V_{CC} and V_{CCIO} .
2. $0 < V_{CC} < V_{CC}$ (MAX), $0 < V_{CCIO} < V_{CCIO}$ (MAX).
3. I_{DK} is additive to I_{PU} , I_{PD} or I_{BH} .

ESD Performance

Please refer to the [MachXO2 Product Family Qualification Summary](#) for complete qualification data, including ESD performance.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
$I_{IL}, I_{IH}^{1,4}$	Input or I/O Leakage	Clamp OFF and $V_{CCIO} < V_{IN} < V_{IH} (MAX)$	—	—	+175	μA
		Clamp OFF and $V_{IN} = V_{CCIO}$	-10	—	10	μA
		Clamp OFF and $V_{CCIO} - 0.97 V < V_{IN} < V_{CCIO}$	-175	—	—	μA
		Clamp OFF and $0 V < V_{IN} < V_{CCIO} - 0.97 V$	—	—	10	μA
		Clamp OFF and $V_{IN} = GND$	—	—	10	μA
		Clamp ON and $0 V < V_{IN} < V_{CCIO}$	—	—	10	μA
I_{PU}	I/O Active Pull-up Current	$0 < V_{IN} < 0.7 V_{CCIO}$	-30	—	-309	μA
I_{PD}	I/O Active Pull-down Current	$V_{IL} (MAX) < V_{IN} < V_{CCIO}$	30	—	305	μA
I_{BHLS}	Bus Hold Low sustaining current	$V_{IN} = V_{IL} (MAX)$	30	—	—	μA
I_{BHHS}	Bus Hold High sustaining current	$V_{IN} = 0.7V_{CCIO}$	-30	—	—	μA
I_{BHLO}	Bus Hold Low Overdrive current	$0 \leq V_{IN} \leq V_{CCIO}$	—	—	305	μA
I_{BHHO}	Bus Hold High Overdrive current	$0 \leq V_{IN} \leq V_{CCIO}$	—	—	-309	μA
V_{BHT}^3	Bus Hold Trip Points		$V_{IL} (MAX)$	—	$V_{IH} (MIN)$	V
C1	I/O Capacitance ²	$V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 \text{ to } V_{IH} (MAX)$	3	5	9	pf
C2	Dedicated Input Capacitance ²	$V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 \text{ to } V_{IH} (MAX)$	3	5.5	7	pf
V_{HYST}	Hysteresis for Schmitt Trigger Inputs ⁵	$V_{CCIO} = 3.3 V, \text{Hysteresis} = \text{Large}$	—	450	—	mV
		$V_{CCIO} = 2.5 V, \text{Hysteresis} = \text{Large}$	—	250	—	mV
		$V_{CCIO} = 1.8 V, \text{Hysteresis} = \text{Large}$	—	125	—	mV
		$V_{CCIO} = 1.5 V, \text{Hysteresis} = \text{Large}$	—	100	—	mV
		$V_{CCIO} = 3.3 V, \text{Hysteresis} = \text{Small}$	—	250	—	mV
		$V_{CCIO} = 2.5 V, \text{Hysteresis} = \text{Small}$	—	150	—	mV
		$V_{CCIO} = 1.8 V, \text{Hysteresis} = \text{Small}$	—	60	—	mV
		$V_{CCIO} = 1.5 V, \text{Hysteresis} = \text{Small}$	—	40	—	mV

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. $T_A = 25^\circ C$, $f = 1.0 \text{ MHz}$.
3. Please refer to V_{IL} and V_{IH} in the sysIO Single-Ended DC Electrical Characteristics table of this document.
4. When V_{IH} is higher than V_{CCIO} , a transient current typically of 30 ns in duration or less with a peak current of 6mA can occur on the high-to-low transition. For true LVDS output pins in MachXO3L/LF devices, V_{IH} must be less than or equal to V_{CCIO} .
5. With bus keeper circuit turned on. For more details, refer to TN1280, [MachXO3 sysIO Usage Guide](#).

sysIO Recommended Operating Conditions

Standard	V _{CCIO} (V)			V _{REF} (V)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
LVC MOS 3.3	3.135	3.3	3.465	—	—	—
LVC MOS 2.5	2.375	2.5	2.625	—	—	—
LVC MOS 1.8	1.71	1.8	1.89	—	—	—
LVC MOS 1.5	1.425	1.5	1.575	—	—	—
LVC MOS 1.2	1.14	1.2	1.26	—	—	—
LVTTL	3.135	3.3	3.465	—	—	—
LVDS25 ^{1, 2}	2.375	2.5	2.625	—	—	—
LVDS33 ^{1, 2}	3.135	3.3	3.465	—	—	—
LVPECL ¹	3.135	3.3	3.465	—	—	—
BLVDS ¹	2.375	2.5	2.625	—	—	—
MIPI ³	2.375	2.5	2.625	—	—	—
MIPI_LP ³	1.14	1.2	1.26	—	—	—
LVC MOS25R33	3.135	3.3	3.6	1.1	1.25	1.4
LVC MOS18R33	3.135	3.3	3.6	0.75	0.9	1.05
LVC MOS18R25	2.375	2.5	2.625	0.75	0.9	1.05
LVC MOS15R33	3.135	3.3	3.6	0.6	0.75	0.9
LVC MOS15R25	2.375	2.5	2.625	0.6	0.75	0.9
LVC MOS12R33 ⁴	3.135	3.3	3.6	0.45	0.6	0.75
LVC MOS12R25 ⁴	2.375	2.5	2.625	0.45	0.6	0.75
LVC MOS10R33 ⁴	3.135	3.3	3.6	0.35	0.5	0.65
LVC MOS10R25 ⁴	2.375	2.5	2.625	0.35	0.5	0.65

1. Inputs on-chip. Outputs are implemented with the addition of external resistors.

2. For the dedicated LVDS buffers.

3. Requires the addition of external resistors.

4. Supported only for inputs and BIDs for -6 speed grade devices.

sysIO Single-Ended DC Electrical Characteristics^{1, 2}

Input/Output Standard	V _{IL}		V _{IH}		V _{OL} Max. (V)	V _{OH} Min. (V)	I _{OL} Max. ⁴ (mA)	I _{OH} Max. ⁴ (mA)
	Min. (V) ³	Max. (V)	Min. (V)	Max. (V)				
LVCMOS 3.3 LVTTL	-0.3	0.8	2.0	3.6	0.4	V _{CCIO} - 0.4	4	-4
							8	-8
							12	-12
							16	-16
LVCMOS 2.5	-0.3	0.7	1.7	3.6	0.4	V _{CCIO} - 0.4	0.1	-0.1
							4	-4
							8	-8
							12	-12
LVCMOS 1.8	-0.3	0.35V _{CCIO}	0.65V _{CCIO}	3.6	0.4	V _{CCIO} - 0.4	16	-16
							0.1	-0.1
							4	-4
							8	-8
LVCMOS 1.5	-0.3	0.35V _{CCIO}	0.65V _{CCIO}	3.6	0.4	V _{CCIO} - 0.4	12	-12
							0.1	-0.1
							4	-4
							8	-8
LVCMOS 1.2	-0.3	0.35V _{CCIO}	0.65V _{CCIO}	3.6	0.4	V _{CCIO} - 0.4	0.1	-0.1
							4	-2
							8	-6
							0.1	-0.1
LVCMOS25R33	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS18R33	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS18R25	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS15R33	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS15R25	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS12R33	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS12R25	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain
LVCMOS10R33	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS10R25	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain

1. MachXO3L/LF devices allow LVCMOS inputs to be placed in I/O banks where V_{CCIO} is different from what is specified in the applicable JEDEC specification. This is referred to as a ratioed input buffer. In a majority of cases this operation follows or exceeds the applicable JEDEC specification. The cases where MachXO3L/LF devices do not meet the relevant JEDEC specification are documented in the table below.
2. MachXO3L/LF devices allow for LVCMOS referenced I/Os which follow applicable JEDEC specifications. For more details about mixed mode operation please refer to please refer to TN1280, [MachXO3 sysIO Usage Guide](#).
3. The dual function I²C pins SCL and SDA are limited to a V_{IL} min of -0.25 V or to -0.3 V with a duration of <10 ns.
4. For electromigration, the average DC current sourced or sinked by I/O pads between two consecutive V_{CCIO} or GND pad connections, or between the last V_{CCIO} or GND in an I/O bank and the end of an I/O bank, as shown in the Logic Signal Connections table (also shown as I/O grouping) shall not exceed a maximum of n * 8 mA. "n" is the number of I/O pads between the two consecutive bank V_{CCIO} or GND connections or between the last V_{CCIO} and GND in a bank and the end of a bank. IO Grouping can be found in the Data Sheet Pin Tables, which can also be generated from the Lattice Diamond software.

MIPI D-PHY Emulation

MachXO3L/LF devices can support MIPI D-PHY unidirectional HS (High Speed) and bidirectional LP (Low Power) inputs and outputs via emulation. In conjunction with external resistors High Speed IOs use the LVDS25E buffer and Low Power IOs use the LVC MOS buffers. The scheme shown in Figure 3-4 is one possible solution for MIPI D-PHY Receiver implementation. The scheme shown in Figure 3-5 is one possible solution for MIPI D-PHY Transmitter implementation.

Figure 3-4. MIPI D-PHY Input Using External Resistors

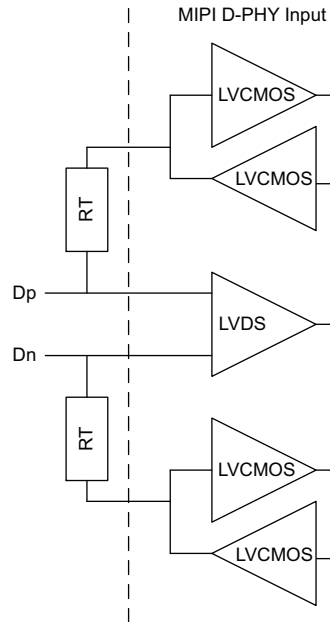


Table 3-4. MIPI DC Conditions¹

	Description	Min.	Typ.	Max.	Units
Receiver					
External Termination					
RT	1% external resistor with VCCIO=2.5 V	—	50	—	Ohms
	1% external resistor with VCCIO=3.3 V	—	50	—	Ohms
High Speed					
VCCIO	VCCIO of the Bank with LVDS Emulated input buffer	—	2.5	—	V
	VCCIO of the Bank with LVDS Emulated input buffer	—	3.3	—	V
VCMRX	Common-mode voltage HS receive mode	150	200	250	mV
VIDTH	Differential input high threshold	—	—	100	mV
VIDTL	Differential input low threshold	-100	—	—	mV
VIHHS	Single-ended input high voltage	—	—	300	mV
VILHS	Single-ended input low voltage	100	—	—	mV
ZID	Differential input impedance	80	100	120	Ohms

Maximum sysIO Buffer Performance

I/O Standard	Max. Speed	Units
MIPI	450	MHz
LVDS25	400	MHz
LVDS25E	150	MHz
BLVDS25	150	MHz
BLVDS25E	150	MHz
MLVDS25	150	MHz
MLVDS25E	150	MHz
LVPECL33	150	MHz
LVPECL33E	150	MHz
LVTTL33	150	MHz
LVTTL33D	150	MHz
LVC MOS33	150	MHz
LVC MOS33D	150	MHz
LVC MOS25	150	MHz
LVC MOS25D	150	MHz
LVC MOS18	150	MHz
LVC MOS18D	150	MHz
LVC MOS15	150	MHz
LVC MOS15D	150	MHz
LVC MOS12	91	MHz
LVC MOS12D	91	MHz

Parameter	Description	Device	-6		-5		Units
			Min.	Max.	Min.	Max.	
General I/O Pin Parameters (Using Edge Clock without PLL)							
t _{COE}	Clock to Output - PIO Output Register	MachXO3L/LF-1300	—	7.53	—	7.76	ns
		MachXO3L/LF-2100	—	7.53	—	7.76	ns
		MachXO3L/LF-4300	—	7.45	—	7.68	ns
		MachXO3L/LF-6900	—	7.53	—	7.76	ns
		MachXO3L/LF-9400	—	8.93	—	9.35	ns
t _{SUE}	Clock to Data Setup - PIO Input Register	MachXO3L/LF-1300	−0.19	—	−0.19	—	ns
		MachXO3L/LF-2100	−0.19	—	−0.19	—	ns
		MachXO3L/LF-4300	−0.16	—	−0.16	—	ns
		MachXO3L/LF-6900	−0.19	—	−0.19	—	ns
		MachXO3L/LF-9400	−0.20	—	−0.20	—	ns
t _{HE}	Clock to Data Hold - PIO Input Register	MachXO3L/LF-1300	1.97	—	2.24	—	ns
		MachXO3L/LF-2100	1.97	—	2.24	—	ns
		MachXO3L/LF-4300	1.89	—	2.16	—	ns
		MachXO3L/LF-6900	1.97	—	2.24	—	ns
		MachXO3L/LF-9400	1.98	—	2.25	—	ns
t _{SU_DELE}	Clock to Data Setup - PIO Input Register with Data Input Delay	MachXO3L/LF-1300	1.56	—	1.69	—	ns
		MachXO3L/LF-2100	1.56	—	1.69	—	ns
		MachXO3L/LF-4300	1.74	—	1.88	—	ns
		MachXO3L/LF-6900	1.66	—	1.81	—	ns
		MachXO3L/LF-9400	1.71	—	1.85	—	ns
t _{H_DELE}	Clock to Data Hold - PIO Input Register with Input Data Delay	MachXO3L/LF-1300	−0.23	—	−0.23	—	ns
		MachXO3L/LF-2100	−0.23	—	−0.23	—	ns
		MachXO3L/LF-4300	−0.34	—	−0.34	—	ns
		MachXO3L/LF-6900	−0.29	—	−0.29	—	ns
		MachXO3L/LF-9400	−0.30	—	−0.30	—	ns
General I/O Pin Parameters (Using Primary Clock with PLL)							
t _{COPLL}	Clock to Output - PIO Output Register	MachXO3L/LF-1300	—	5.98	—	6.01	ns
		MachXO3L/LF-2100	—	5.98	—	6.01	ns
		MachXO3L/LF-4300	—	5.99	—	6.02	ns
		MachXO3L/LF-6900	—	6.02	—	6.06	ns
		MachXO3L/LF-9400	—	5.55	—	6.13	ns
t _{SUPLL}	Clock to Data Setup - PIO Input Register	MachXO3L/LF-1300	0.36	—	0.36	—	ns
		MachXO3L/LF-2100	0.36	—	0.36	—	ns
		MachXO3L/LF-4300	0.35	—	0.35	—	ns
		MachXO3L/LF-6900	0.34	—	0.34	—	ns
		MachXO3L/LF-9400	0.33	—	0.33	—	ns
t _{HPLL}	Clock to Data Hold - PIO Input Register	MachXO3L/LF-1300	0.42	—	0.49	—	ns
		MachXO3L/LF-2100	0.42	—	0.49	—	ns
		MachXO3L/LF-4300	0.43	—	0.50	—	ns
		MachXO3L/LF-6900	0.46	—	0.54	—	ns
		MachXO3L/LF-9400	0.47	—	0.55	—	ns

Parameter	Description	Device	-6		-5		Units
			Min.	Max.	Min.	Max.	
MIPI D-PHY Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input - GDDR4_RX.ECLK.Centered ^{10, 11, 12}							
t _{SU} ¹⁵	Input Data Setup Before ECLK	All MachXO3L/LF devices, bottom side only	0.200	—	0.200	—	UI
t _{HO} ¹⁵	Input Data Hold After ECLK		0.200	—	0.200	—	UI
f _{DATA} ¹⁴	MIPI D-PHY Input Data Speed		—	900	—	900	Mbps
f _{DDR4} ¹⁴	MIPI D-PHY ECLK Frequency		—	450	—	450	MHz
f _{SCLK} ¹⁴	SCLK Frequency		—	112.5	—	112.5	MHz
Generic DDR Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDR1_TX.SCLK.Aligned ⁸							
t _{DIA}	Output Data Invalid After CLK Output	All MachXO3L/LF devices, all sides	—	0.520	—	0.550	ns
t _{DIB}	Output Data Invalid Before CLK Output		—	0.520	—	0.550	ns
f _{DATA}	DDR1 Output Data Speed		—	300	—	250	Mbps
f _{DDR1}	DDR1 SCLK frequency		—	150	—	125	MHz
Generic DDR Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDR1_TX.SCLK.Centered ⁸							
t _{DVB}	Output Data Valid Before CLK Output	All MachXO3L/LF devices, all sides	1.210	—	1.510	—	ns
t _{DVA}	Output Data Valid After CLK Output		1.210	—	1.510	—	ns
f _{DATA}	DDR1 Output Data Speed		—	300	—	250	Mbps
f _{DDR1}	DDR1 SCLK Frequency (minimum limited by PLL)		—	150	—	125	MHz
Generic DDR2 Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDR2_TX.ECLK.Aligned ⁸							
t _{DIA}	Output Data Invalid After CLK Output	MachXO3L/LF devices, top side only	—	0.200	—	0.215	ns
t _{DIB}	Output Data Invalid Before CLK Output		—	0.200	—	0.215	ns
f _{DATA}	DDR2 Serial Output Data Speed		—	664	—	554	Mbps
f _{DDR2}	DDR2 ECLK frequency		—	332	—	277	MHz
f _{SCLK}	SCLK Frequency		—	166	—	139	MHz
Generic DDR2 Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDR2_TX.ECLK.Centered ^{8, 9}							
t _{DVB}	Output Data Valid Before CLK Output	MachXO3L/LF devices, top side only	0.535	—	0.670	—	ns
t _{DVA}	Output Data Valid After CLK Output		0.535	—	0.670	—	ns
f _{DATA}	DDR2 Serial Output Data Speed		—	664	—	554	Mbps
f _{DDR2}	DDR2 ECLK Frequency (minimum limited by PLL)		—	332	—	277	MHz
f _{SCLK}	SCLK Frequency		—	166	—	139	MHz
Generic DDR4 Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDR4_TX.ECLK.Aligned ^{8, 9}							
t _{DIA}	Output Data Invalid After CLK Output	MachXO3L/LF devices, top side only	—	0.200	—	0.215	ns
t _{DIB}	Output Data Invalid Before CLK Output		—	0.200	—	0.215	ns
f _{DATA}	DDR4 Serial Output Data Speed		—	800	—	630	Mbps
f _{DDR4}	DDR4 ECLK Frequency		—	400	—	315	MHz
f _{SCLK}	SCLK Frequency		—	100	—	79	MHz

sysCONFIG Port Timing Specifications

Symbol	Parameter		Min.	Max.	Units
All Configuration Modes					
t _{PRGM}	PROGRAMN low pulse accept		55	—	ns
t _{PRGMJ}	PROGRAMN low pulse rejection		—	25	ns
t _{INITL}	INITN low time	LCMXO3L/LF-640/ LCMXO3L/LF-1300	—	55	us
		LCMXO3L/LF-1300 256-Ball Package/ LCMXO3L/LF-2100	—	70	us
		LCMXO3L/LF-2100 324-Ball Package/ LCMXO3-4300	—	105	us
		LCMXO3L/LF-4300 400-Ball Package/ LCMXO3-6900	—	130	us
		LCMXO3L/LF-9400C	—	175	us
t _{DPPINIT}	PROGRAMN low to INITN low		—	150	ns
t _{DPPDONE}	PROGRAMN low to DONE low		—	150	ns
t _{IODISS}	PROGRAMN low to I/O disable		—	120	ns
Slave SPI					
f _{MAX}	CCLK clock frequency		—	66	MHz
t _{CCLKH}	CCLK clock pulse width high		7.5	—	ns
t _{CCLKL}	CCLK clock pulse width low		7.5	—	ns
t _{STSU}	CCLK setup time		2	—	ns
t _{STH}	CCLK hold time		0	—	ns
t _{STCO}	CCLK falling edge to valid output		—	10	ns
t _{STOZ}	CCLK falling edge to valid disable		—	10	ns
t _{STOV}	CCLK falling edge to valid enable		—	10	ns
t _{SCS}	Chip select high time		25	—	ns
t _{SCSS}	Chip select setup time		3	—	ns
t _{SCSH}	Chip select hold time		3	—	ns
Master SPI					
f _{MAX}	MCLK clock frequency		—	133	MHz
t _{MCLKH}	MCLK clock pulse width high		3.75	—	ns
t _{MCLKL}	MCLK clock pulse width low		3.75	—	ns
t _{STSU}	MCLK setup time		5	—	ns
t _{STH}	MCLK hold time		1	—	ns
t _{CSSPI}	INITN high to chip select low		100	200	ns
t _{MCLK}	INITN high to first MCLK edge		0.75	1	us

Signal Descriptions (Cont.)

Signal Name	I/O	Descriptions
Configuration (Dual function pins used during sysCONFIG)		
PROGRAMN	I	Initiates configuration sequence when asserted low. This pin always has an active pull-up.
INITN	I/O	Open Drain pin. Indicates the FPGA is ready to be configured. During configuration, a pull-up is enabled.
DONE	I/O	Open Drain pin. Indicates that the configuration sequence is complete, and the start-up sequence is in progress.
MCLK/CCLK	I/O	Input Configuration Clock for configuring an FPGA in Slave SPI mode. Output Configuration Clock for configuring an FPGA in SPI and SPIm configuration modes.
SN	I	Slave SPI active low chip select input.
CSSPIN	I/O	Master SPI active low chip select output.
SI/SPISI	I/O	Slave SPI serial data input and master SPI serial data output.
SO/SPISO	I/O	Slave SPI serial data output and master SPI serial data input.
SCL	I/O	Slave I ² C clock input and master I ² C clock output.
SDA	I/O	Slave I ² C data input and master I ² C data output.

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3LF-6900E-5MG256C	6900	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3LF-6900E-6MG256C	6900	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3LF-6900E-5MG256I	6900	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3LF-6900E-6MG256I	6900	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3LF-6900E-5MG324C	6900	1.2 V	5	Halogen-Free csfBGA	324	COM
LCMXO3LF-6900E-6MG324C	6900	1.2 V	6	Halogen-Free csfBGA	324	COM
LCMXO3LF-6900E-5MG324I	6900	1.2 V	5	Halogen-Free csfBGA	324	IND
LCMXO3LF-6900E-6MG324I	6900	1.2 V	6	Halogen-Free csfBGA	324	IND
LCMXO3LF-6900C-5BG256C	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3LF-6900C-6BG256C	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3LF-6900C-5BG256I	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3LF-6900C-6BG256I	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	IND
LCMXO3LF-6900C-5BG324C	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	COM
LCMXO3LF-6900C-6BG324C	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	COM
LCMXO3LF-6900C-5BG324I	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	IND
LCMXO3LF-6900C-6BG324I	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	IND
LCMXO3LF-6900C-5BG400C	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	400	COM
LCMXO3LF-6900C-6BG400C	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	400	COM
LCMXO3LF-6900C-5BG400I	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	400	IND
LCMXO3LF-6900C-6BG400I	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	400	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3LF-9400E-5MG256C	9400	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3LF-9400E-6MG256C	9400	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3LF-9400E-5MG256I	9400	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3LF-9400E-6MG256I	9400	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3LF-9400C-5BG256C	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3LF-9400C-6BG256C	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3LF-9400C-5BG256I	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3LF-9400C-6BG256I	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	256	IND
LCMXO3LF-9400C-5BG400C	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	400	COM
LCMXO3LF-9400C-6BG400C	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	400	COM
LCMXO3LF-9400C-5BG400I	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	400	IND
LCMXO3LF-9400C-6BG400I	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	400	IND
LCMXO3LF-9400C-5BG484C	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	484	COM
LCMXO3LF-9400C-6BG484C	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	484	COM
LCMXO3LF-9400C-5BG484I	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	484	IND
LCMXO3LF-9400C-6BG484I	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	484	IND

MachXO3 Family Data Sheet

Revision History

February 2017

Advance Data Sheet DS1047

Date	Version	Section	Change Summary
February 2017	1.8	Architecture	Updated Supported Standards section. Corrected “MDVS” to “MLDVS” in Table 2-11, Supported Input Standards.
		DC and Switching Characteristics	Updated ESD Performance section. Added reference to the MachXO2 Product Family Qualification Summary document.
			Updated Static Supply Current – C/E Devices section. Added footnote 7.
			Updated MachXO3L/LF External Switching Characteristics – C/E Devices section. — Populated values for MachXO3L/LF-9400. — Under 7:1 LVDS Outputs – GDDR71_TX.ECLK.7:1, corrected “t _{DVB} ” to “t _{DIB} ” and “t _{DVA} ” to “t _{DIA} ” and revised their descriptions. — Added Figure 3-6, Receiver GDDR71_RX Waveforms and Figure 3-7, Transmitter GDDR71_TX Waveforms.
		Pinout Information	Updated the Pin Information Summary section. Added MachXO3L/LF-9600C packages.
May 2016	1.7	DC and Switching Characteristics	Updated Absolute Maximum Ratings section. Modified I/O Tri-state Voltage Applied and Dedicated Input Voltage Applied footnotes.
			Updated sysIO Recommended Operating Conditions section. — Added standards. — Added V _{REF} (V) — Added footnote 4.
			Updated sysIO Single-Ended DC Electrical Characteristics section. Added I/O standards.
		Ordering Information	Updated MachXO3L Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging section. Added LCMXO3L-9400C part numbers.
			Updated MachXO3LF Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging section. Added LCMXO3L-9400C part numbers.